

L Number	Hits	Search Text	DB	Time stamp
2	5270	(430/311-313).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 14:18
4	19	((430/311-313).CCLS.) and ((ARC or BARC or anti\$2reflect\$5) same ((Si\$3N or (silicon near nitride)) with poly\$silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 14:30
7	3211	(438/257,260,424,786).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 14:44
8	486	((438/257,260,424,786).CCLS.) and (STI or (trench near isolation)) and ( ARC or rBARC or anti\$2reflect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 14:44
10	127	(((438/257,260,424,786).CCLS.) and (STI or (trench near isolation)) and ( ARC or rBARC or anti\$2reflect\$5)) and (STI or (trench near isolation)) and ( ARC or BARC or anti\$2reflect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 15:02
11	584	(427/255.28).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 15:03
12	2	((427/255.28).CCLS.) and ((ARC or BARC or anti\$2reflect\$5) same ((Si\$3N or (silicon near nitride)) with poly\$silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 15:04
13	306	(resist or photo\$resist) and (Azuma.in. or flaim.in.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 15:05
-	17681	(trench near isolation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:46
-	2973	(trench near isolation) and (pad near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:46

	1870	(trench near isolation) and (pad near oxide) and (poly or poly\$1silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:46
	36	(trench near isolation) and (pad near oxide) and (poly or poly\$1silicon) and (Anti\$4reselect\$7 or BARC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 11:44
	390	(trench near isolation) and (filler same material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:51
	396	(trench near isolation) and (filler same (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:51
	315	(trench near isolation) and (filler with (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:51
	230	(trench near isolation) and (filler near4 (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:52
	146	(trench near isolation) and (filler near (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:52
	31	(trench near isolation) and (pad near oxide) and (poly or poly\$1silicon) and (Anti\$4reselect\$7 or BARC) and (filler or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 21:53
	44	"5886391" or "5930644" or "576262" or EP0908938 or EP0819786	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:31